

General Description

The AGM1030MBP combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

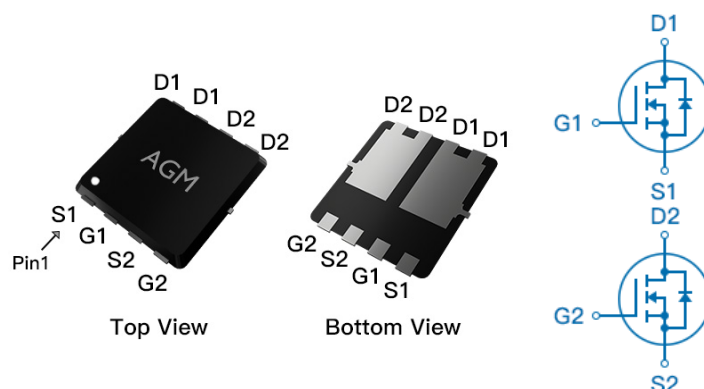
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
100V	26mΩ	20A

PDFN3.3*3.3 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM1030MBP	AGM1030MBP	PDFN3.3*3.3	330mm	12mm	5000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	100	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	20	A
	Drain Current-Continuous(Tc=100°C)	13	A
IDM (pulse)	Drain Current-Pulsed (Note 2)	80	A
PD	Maximum Power Dissipation(Tc=25°C)	50	w
	Maximum Power Dissipation(Tc=100°C)	20	w
EAS	Avalanche energy (Note 3)	30	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	64	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	2.5	°C/W

Table 3. Electrical Characteristics (TJ=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	100	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=100V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	--	2.2	V
gFS	Forward Transconductance	VDS=5V,ID=8A	--	5	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=10A	--	26	32	mΩ
		VGS=4.5V, ID=8A	--	31.5	40	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=50V,VGS=0V, F=1MHZ	--	445	--	pF
Coss	Output Capacitance		--	171	--	pF
Crss	Reverse Transfer Capacitance		--	3.2	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	ID =10A VDS = 50V VGS = 10V RG = 5Ω	--	12	--	nS
tr	Turn-on Rise Time		--	15	--	nS
td(off)	Turn-Off Delay Time		--	20	--	nS
tf	Turn-Off Fall Time		--	6	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=50V, ID=10A	--	8.07	--	nC
Qgs	Gate-Source Charge		--	1.38	--	nC
Qgd	Gate-Drain Charge		--	1.84	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	20	A
VSD	Forward on Voltage	VGS=0V,IS=10A	--	--	1.2	V
trr	Reverse Recovery Time	VDD=50V,Isd=10A , dl/dt=100A/μs , TJ=25℃	--	37	--	ns
Qrr	Reverse Recovery Charge		--	80	--	nc

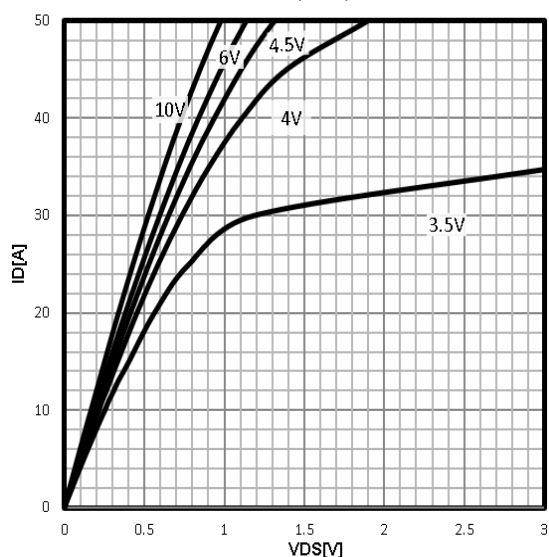
Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

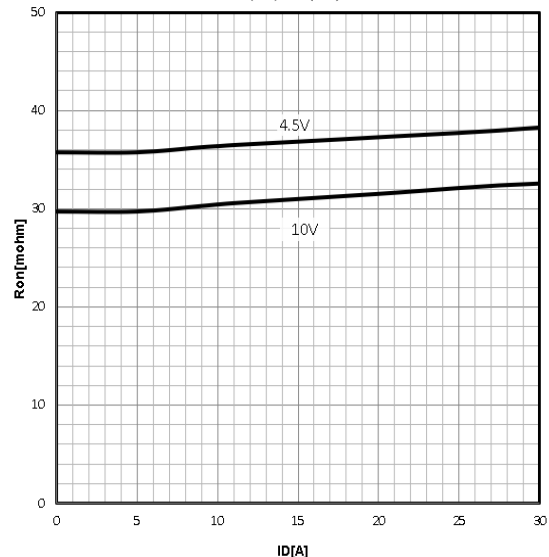
Notes 3.EAS condition: TJ=25°C,VDD=50V,Vgs=10V, ID=11A, L=0.5mH,RG=25ohm

Characteristics Curve:

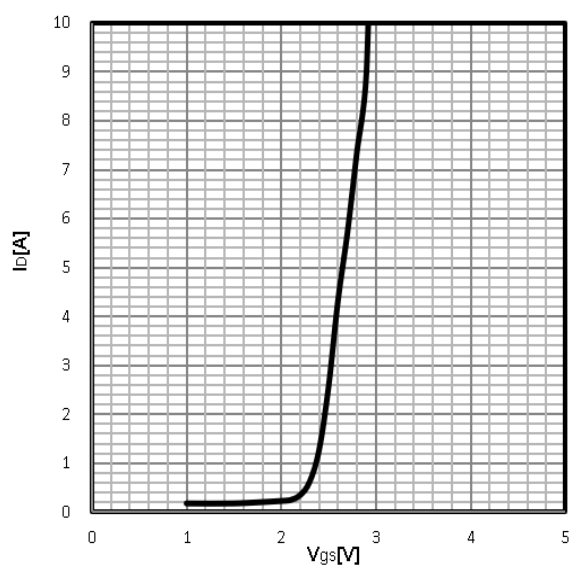
Typ. output characteristics
 $I_D = f(V_{DS})$



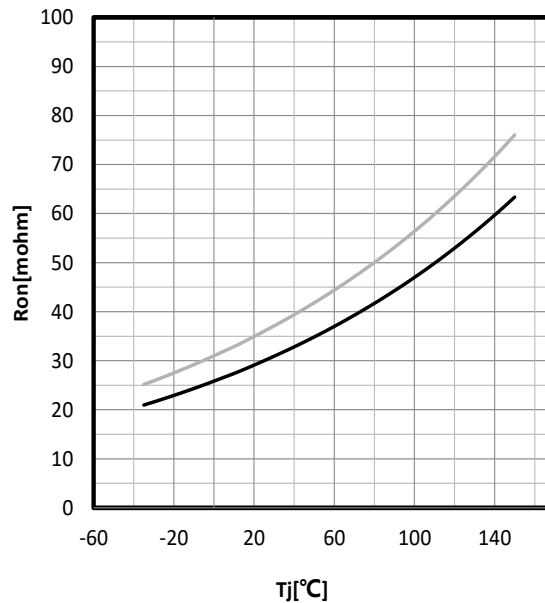
Typ. drain-source on resistance
 $R_{DS(on)} = f(I_D)$



Typ. transfer characteristics
 $I_D = f(V_{GS})$

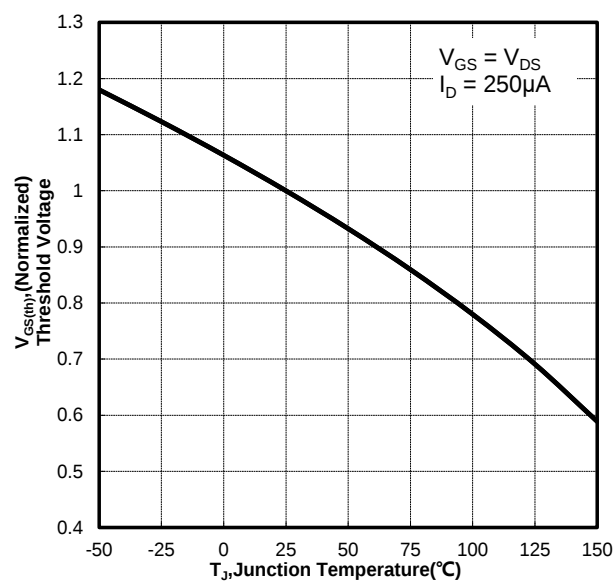


Drain-source on-state resistance
 $R_{DS(on)} = f(T_j); I_D = 10A; V_{GS} = 10V$



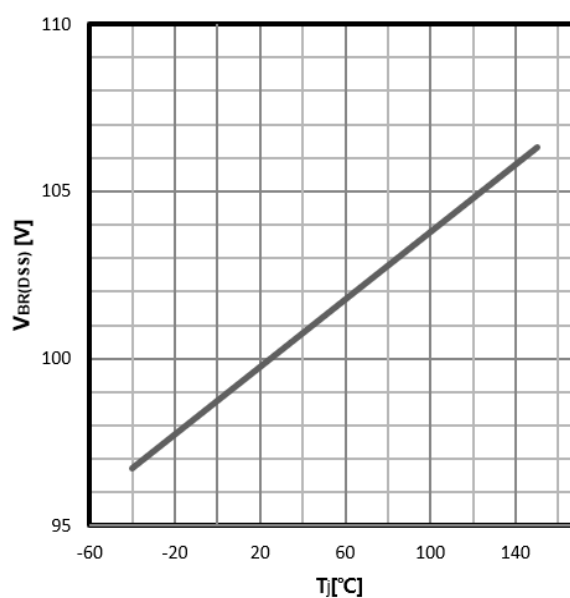
Gate Threshold Voltage

$$V_{TH}=f(T_j); I_D=250\mu A$$



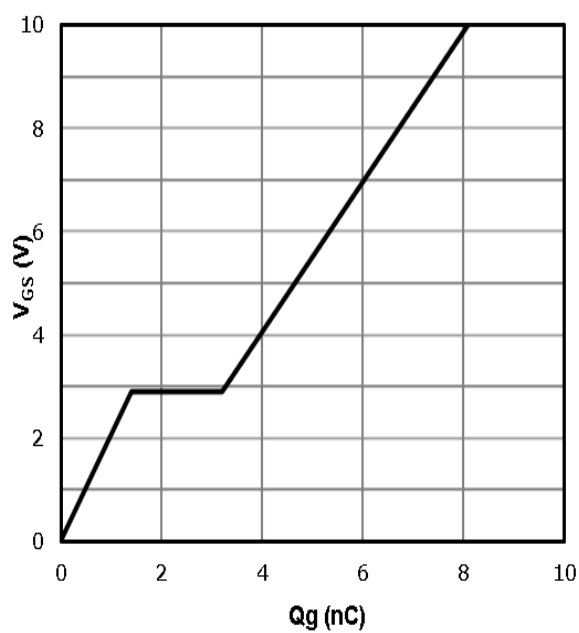
Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=250\mu A$$



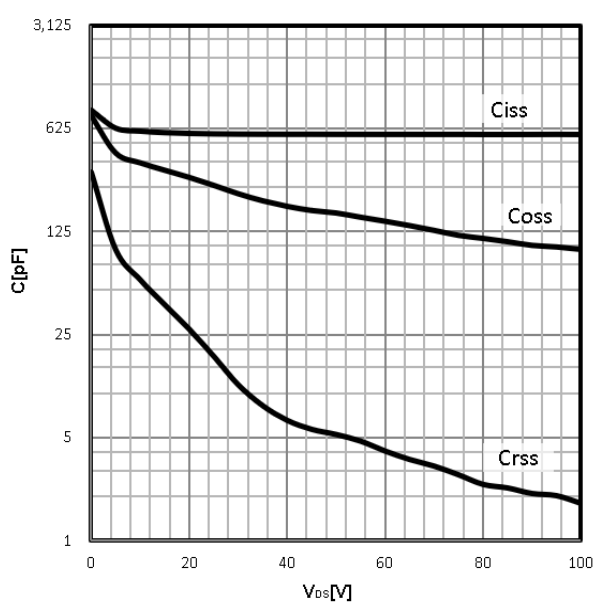
Typ. gate charge

$$V_{GS}=f(Q_g); I_D=10A$$



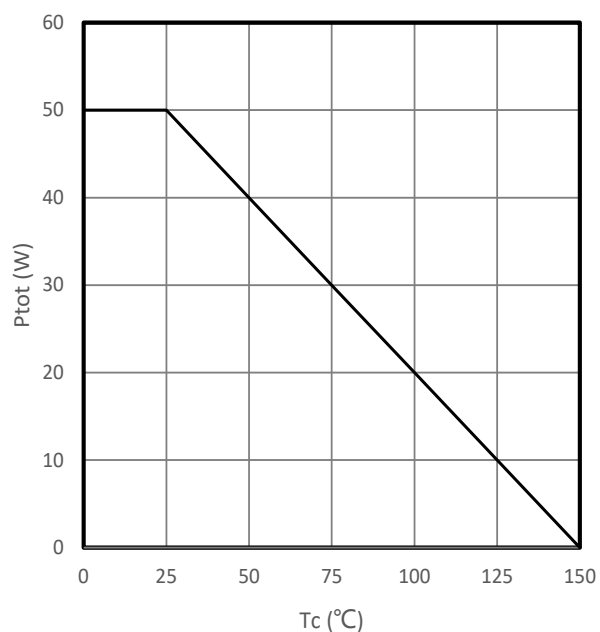
Typ. capacitances

$$C=f(V_{DS}); V_{GS}=0V; f=1MHz$$

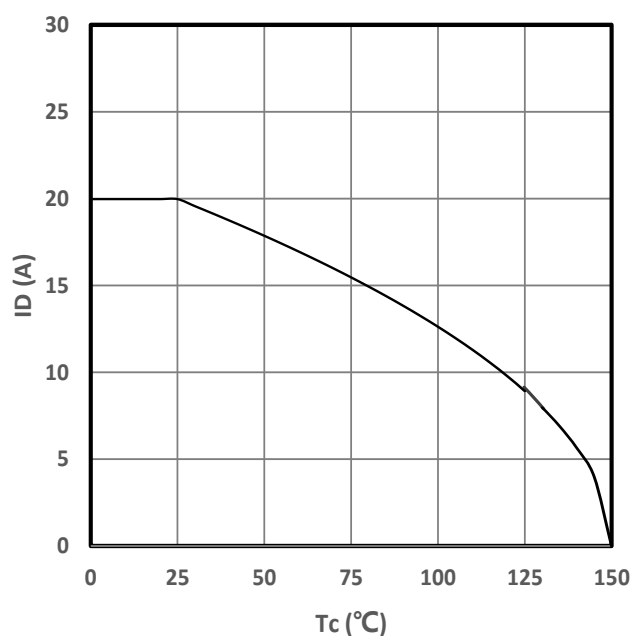


Power Dissipation

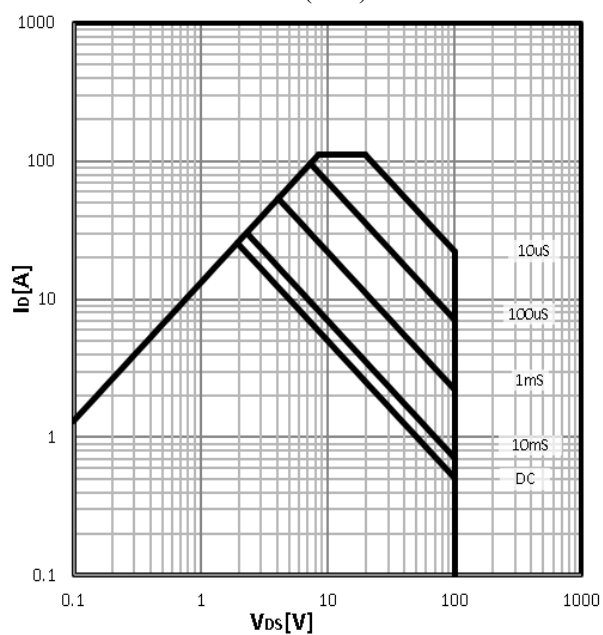
$$P_{tot}=f(T_C)$$


Maximum Drain Current

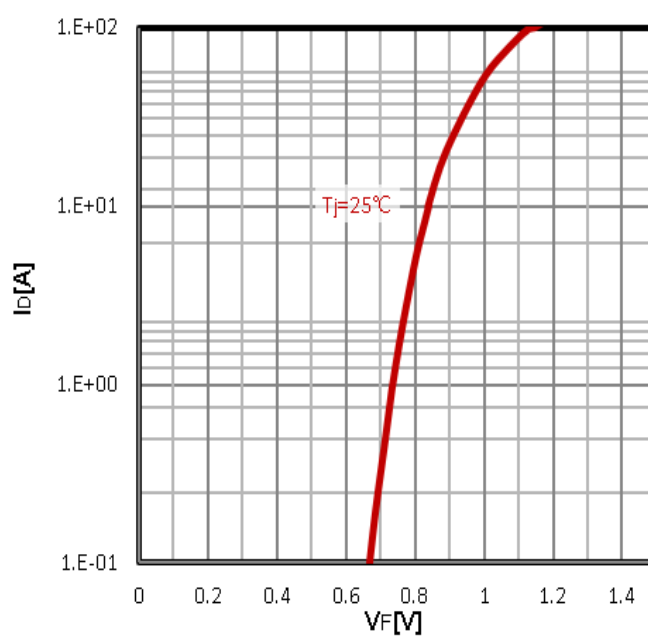
$$I_D=f(T_C)$$


Safe operating area

$$I_D=f(V_{DS})$$

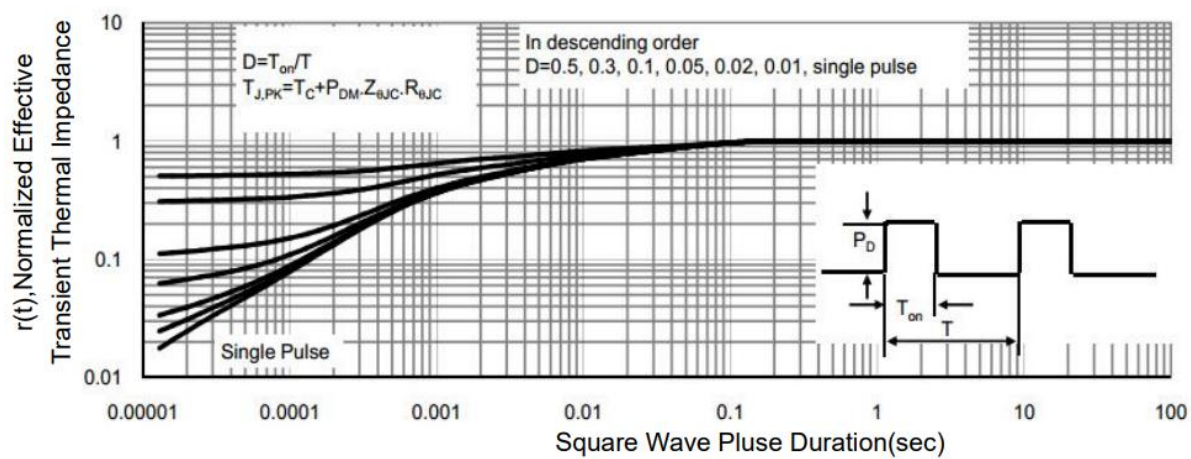

Body Diode Forward Voltage Variation

$$I_F=f(V_{GS})$$

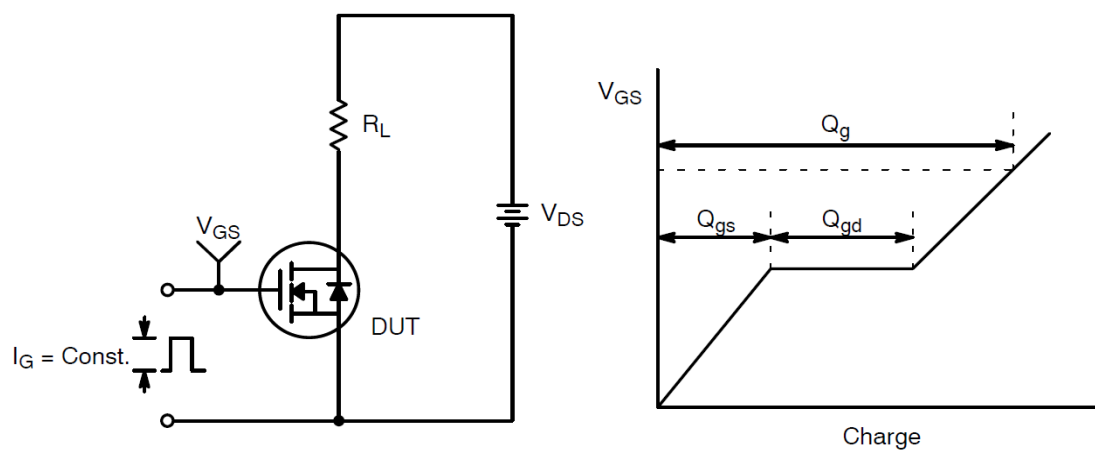


Max. transient thermal impedance

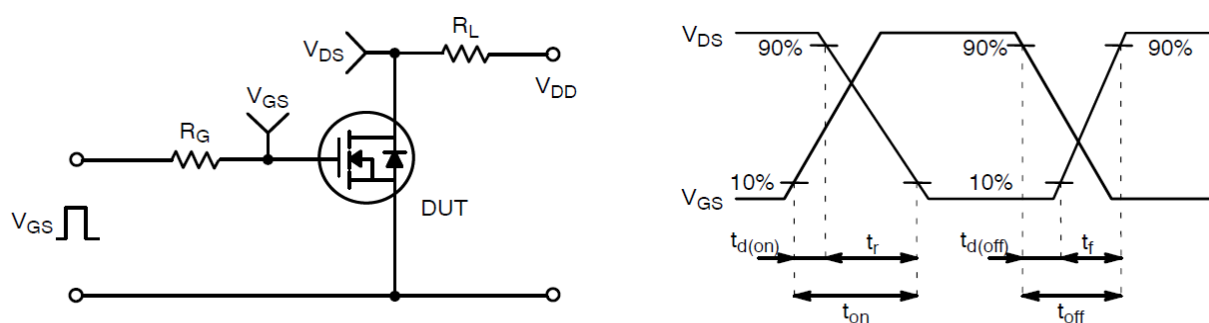
$$Z_{thJC} = f(t_p)$$



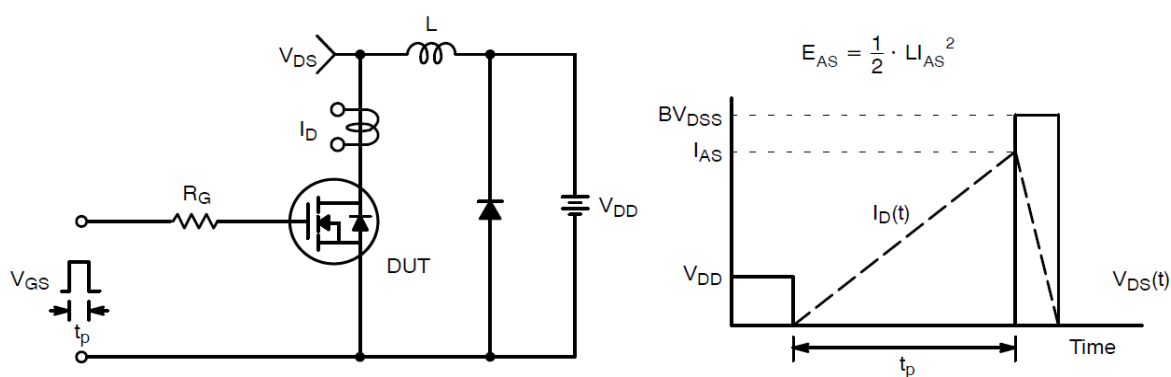
Test Circuit and Waveform:



Gate Charge Test Circuit & Waveform

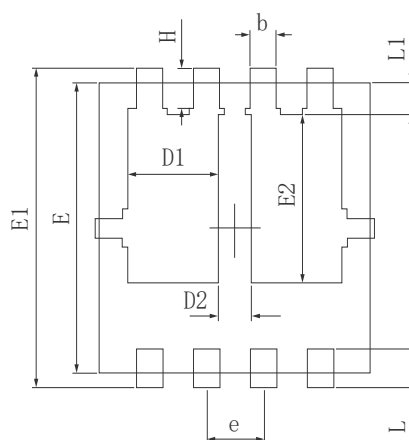
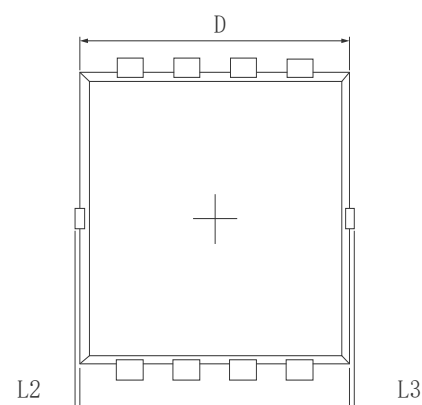


Resistive Switching Test Circuit & Waveforms

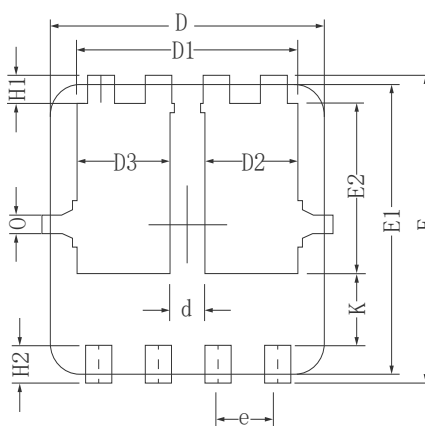
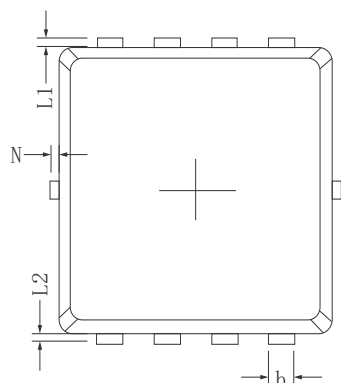
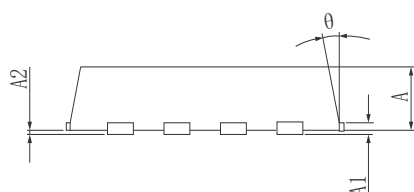


Unclamped Inductive Switching Test Circuit & Waveforms

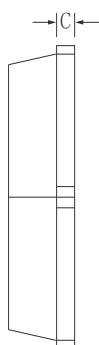
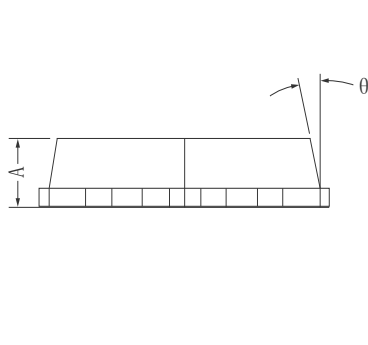
•Dimensions (PDFN3.3*3.3)



SYMBOL	MILLIMETER	
	MIN	MAX
A	0.700	0.900
A1	0.152REF.	
A2	0~0.05	
D	3.000	3.200
D1	0.935	1.135
D2	0.280	0.480
E	2.900	3.100
E1	3.150	3.450
E2	1.535	1.935
b	0.200	0.400
e	0.550	0.750
L	0.300	0.500
L1	0.180	0.480
L2	0~0.100	
L3	0~0.100	
H	0.315	0.515
θ	8°	12°

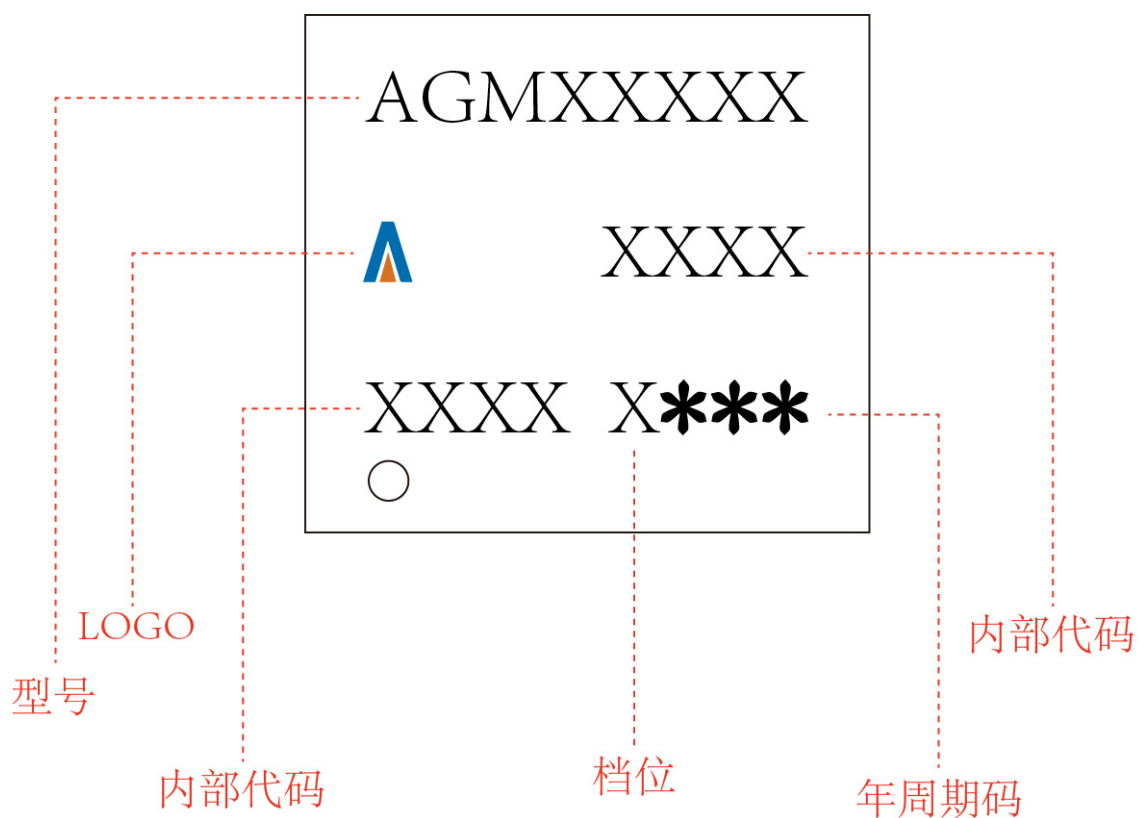


Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	0.65	0.75	0.85
b	0.25	0.30	0.35
C	0.15	0.20	0.25
D	3.00	3.10	3.20
D1	2.40	2.50	2.60
D2/D3	1.00	1.05	1.10
d	0.30	0.40	0.50
E	3.20	3.30	3.40
E1	3.00	3.10	3.20
E2	1.72	1.82	1.92
e	0.65 BSC.		
H1	0.21	0.31	0.41
H2	0.30	0.40	0.50
K	0.67	0.77	0.87
L1/L2	0.10 REF.		
θ	11°	12°	13°
N	0	-	0.15
O	0.2 REF.		



PDFN3.3*3.3

Marking Instructions:



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